

Applicants: Carns et al.  
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**Amendments to the Claims:**

This listing of claims replaces all prior versions and listings of claims in the application.

**Listing of Claims**

Claims 1 – 2 (canceled)

3. (previously presented): A method of forming a capacitor in an integrated circuit comprising:

- (a) forming a lower electrode layer on a semiconductor body;
- (b) forming a dielectric layer over a portion of said lower electrode layer;
- (c) forming an upper electrode layer over a portion of said dielectric layer;
- (d) removing a portion of said upper electrode layer to expose a portion of said dielectric layer, thereby forming an upper electrode with a lateral boundary, wherein a portion of said dielectric layer is disposed in an inter-electrode region, said inter-electrode region disposed within said lateral boundary of said upper electrode and between said lower electrode layer and said upper electrode;
- (e) subsequently removing a portion of said exposed portion of said dielectric layer to expose a portion of said lower electrode layer, wherein a portion of said dielectric layer is removed from said inter-electrode region;
- (f) subsequently forming a conformal insulating layer over a portion of said exposed portion of said lower electrode layer proximate to said portion of said

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